

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	1.8m Ω @10V	150A
	2.2m Ω @4.5V	

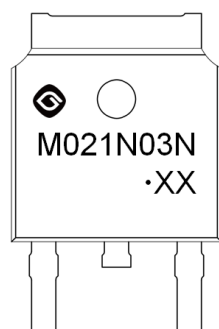
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Switching Application

MARKING:

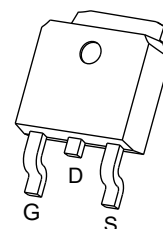


M021N03N = Device Code

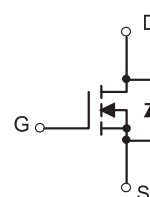
XX = Date Code

Solid Dot = Green Indicator

TO-252-2L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	30	V
Gate - Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	150	A
Continuous Drain Current ¹	$T_C = 100^\circ\text{C}$	I_D	100	A
Pulsed Drain Current ²		I_{DM}	600	A
Single Pulsed Avalanche Current ³		I_{AS}	69	A
Single Pulsed Avalanche Energy ³		E_{AS}	1190	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	156	W
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	0.8	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

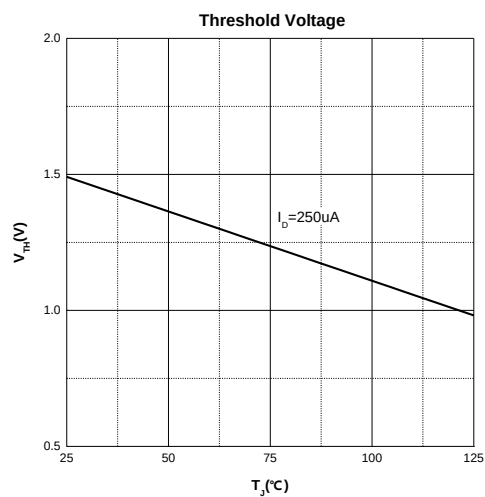
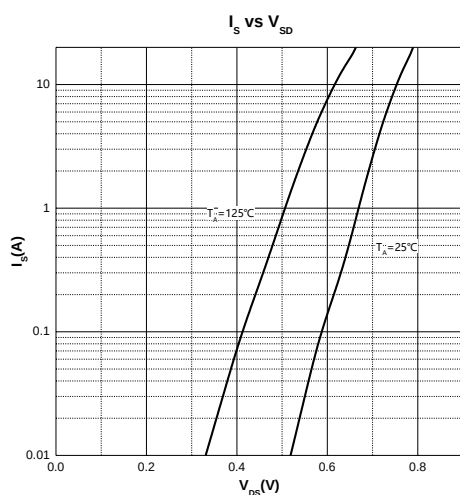
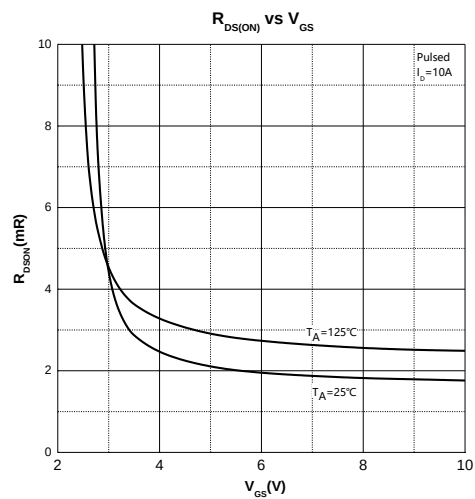
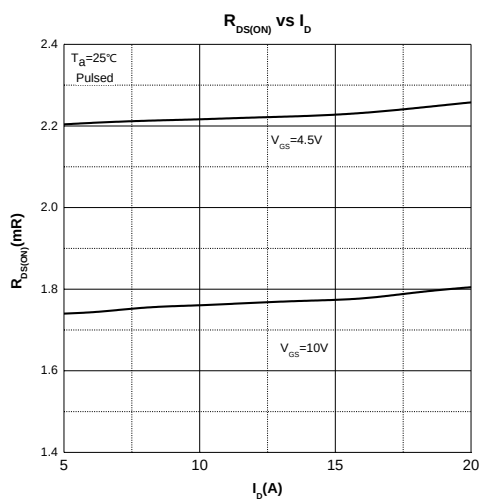
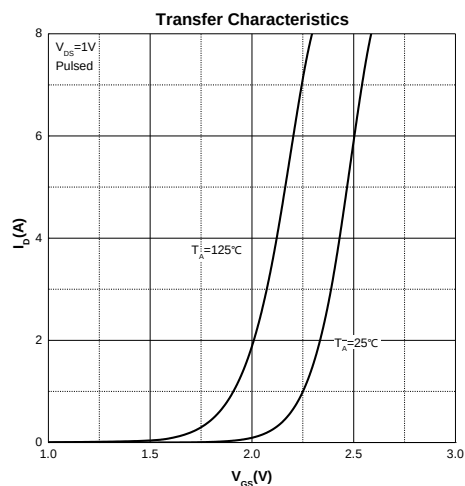
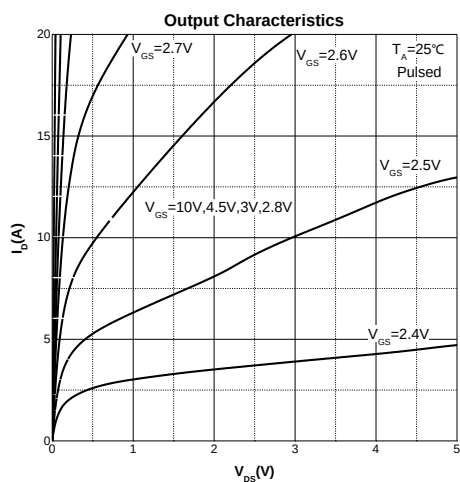
MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

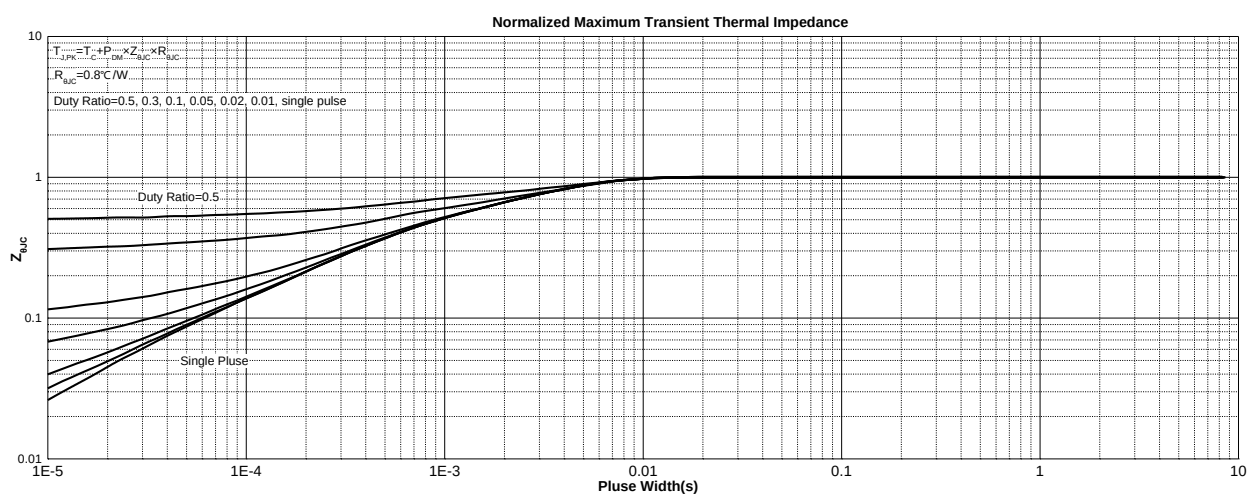
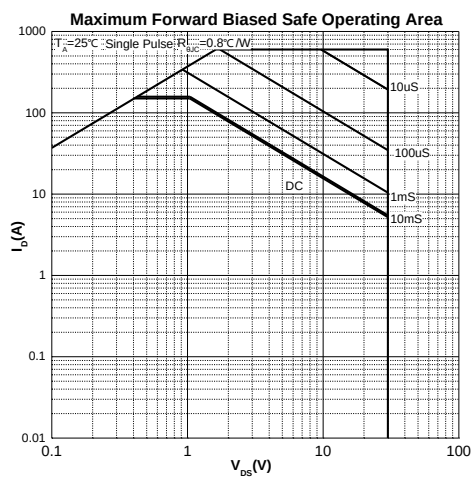
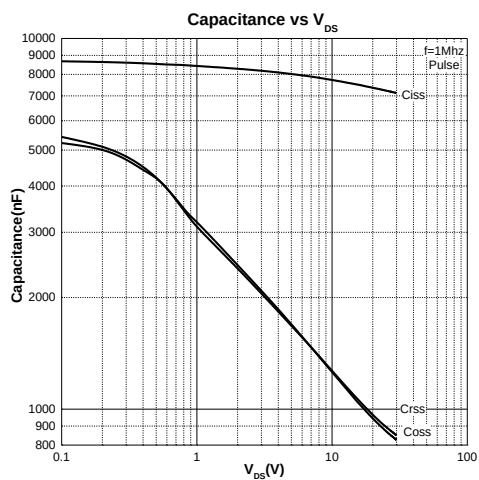
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.5	3.0	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 30A		1.8	2.1	mΩ
		V _{GS} = 4.5V, I _D = 10A		2.2	2.9	
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 10A	10	20		S
Dynamic Characteristics						
Input Capacitance	C _{iSS}	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz		7560		pF
Output Capacitance	C _{oSS}			1064		
Reverse Transfer Capacitance	C _{rSS}			1081		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		1.2		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 15V, V _{GS} = 10V, I _D = 20A		150		nC
Gate-source Charge	Q _{gs}			20		
Gate-drain Charge	Q _{gd}			45		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15V, V _{GS} = 10V, R _L = 0.75Ω R _G = 3Ω		28		ns
Turn-on Rise Time	t _r			36		
Turn-off Delay Ttime	t _{d(off)}			75		
Turn-off Fall Time	t _f			25		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 10A			1.2	V

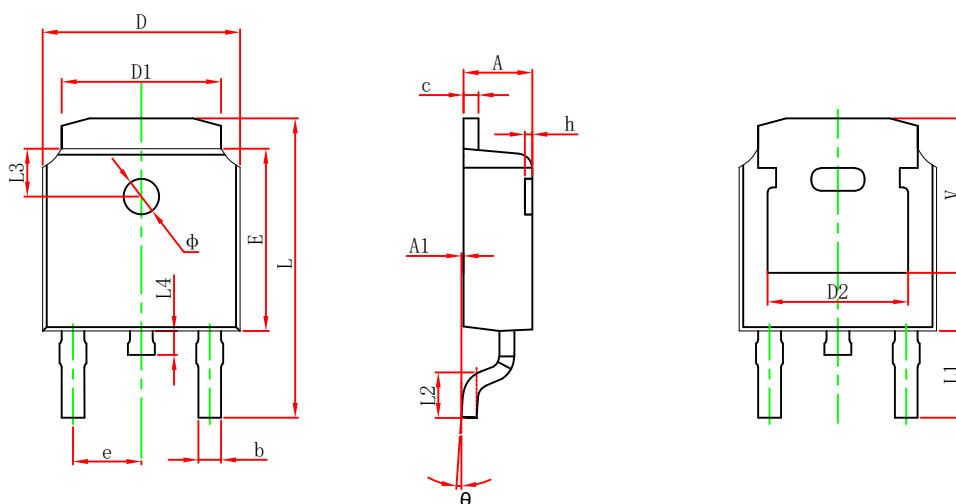
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = 25V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C.And device mounted on a large heatsink
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics





TO-252-2L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	